



A1015GR

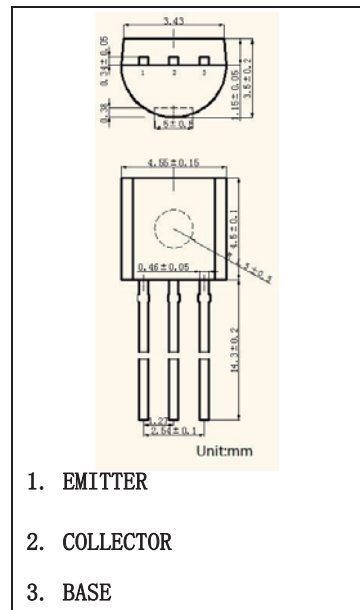
TRANSISTOR(PNP)

FEATURES

Power dissipation

MAXIMUM RATINGS(TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-0.15	A
P _D	Collector Power Dissipation	0.4	W
T _J	Junction Temperature	150	℃
T _{Stg}	Storage Temperature	-55-150	℃



ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100uA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _C =-100uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-100	nA
Collector cut-off current	I _{CEO}	V _{CE} =-50V, I _B =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	H _{FE(1)}	V _{CE} =-6V, I _C =-2mA	70		400	
	H _{FE(2)}	V _{CE} =-6V, I _C =-150mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1.1	V
Gain Bandwidth Product	f _T	V _{CE} =-10V, I _C =-1mA, f=30MHz	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			7	pF
Noise figure	NF	V _{CE} =-6V, I _C =-0.1mA, f=1KHz RG=10KΩ			6	dB

CLASSIFICATION OF H_{FE(1)}

RANK	O	Y	GR
RANGE	70-140	120-240	200-400

Typical Characteristics

